

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

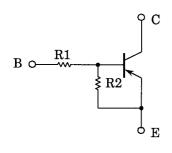
## RN2221,RN2222,RN2223 RN2224,RN2225,RN2226,RN2227

Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

- High current type  $(I_{C(MAX)} = -800 \text{mA})$
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Low VCE (sat)
- Complementary to RN1221~RN1227

## **Equivalent Circuit**

## **Bias Resistor Values**



Type No.	R1 (kΩ)	R2 (kΩ)
RN2221	1	1
RN2222	2.2	2.2
RN2223	4.7	4.7
RN2224	10	10
RN2225	0.47	10
RN2226	1	10
RN2227	2.2	10

# ## 1. EMITTER 2. COLLECTOR 3. BASE JEDEC — EIAJ — TOSHIBA 2-4E1A

Weight: 0.13g

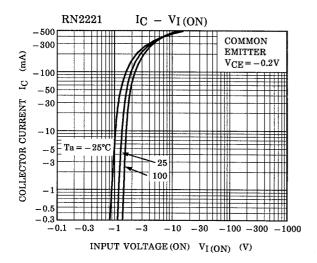
## **Maximum Ratings (Ta = 25°C)**

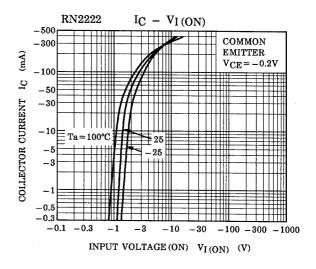
Characteristic		Symbol	Rating	Unit	
Collector-base voltage	RN2221~2227	$V_{CBO}$	-50	V	
Collector-emitter voltage	KINZZZ I ZZZZI	V <sub>CEO</sub>	-50	V	
Emitter-base voltage	RN2221~2224		-10	٧	
	RN2225, 2226	$V_{EBO}$	-5		
	RN2227		-6		
Collector current		I <sub>C</sub>	-800	mA	
Collector power dissipation	RN2221~2227	PC	300	mW	
Junction temperature	ININZZZ I PZZZI	Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

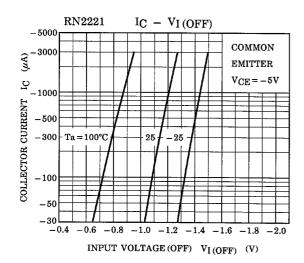


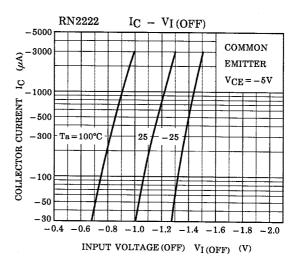
# Electrical Characteristics (Ta = 25°C)

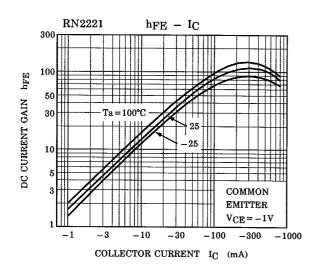
Characteristic	;	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN2221~2227		_	$V_{CB} = -50V, I_E = 0$ $V_{CE} = -50V, I_B = 0$	_	_	-100	nA
	KIN2221~2221		_		_	_	-500	
Emitter cut-off current	RN2221	l <sub>EBO</sub>	_	V <sub>EB</sub> = -10V, I <sub>E</sub> = 0	-3.85	_	-7.14	mA
	RN2222		_		-1.75	_	-3.25	
	RN2223		_		-0.82	_	-1.52	
	RN2224		_		-0.38	_	-0.71	
	RN2225		_	$V_{EB} = -5V$ , $I_{C} = 0$ $V_{EB} = -6V$ , $I_{C} = 0$	-0.365	_	-0.682	
	RN2226		_		-0.35	_	-0.65	
	RN2227		_		-0.378	_	-0.703	
	RN2221		_		60	_	_	
	RN2222		_		65	_	_	
	RN2223		_		70	_	_	
DC current gain	RN2224	$h_{FE}$	_	V <sub>CE</sub> = −1V, I <sub>C</sub> = −100mA	90	_	_	_
, and the second	RN2225		_	10 100	90	_	_	
	RN2226		_		90	_	_	
	RN2227		_		90	_	_	
Collector-emitter saturation voltage	RN2221	V		I <sub>C</sub> = -50mA, I <sub>B</sub> = -2mA			0.05	V
	RN2222~2227	V <sub>CE</sub> (sat)	_	I <sub>C</sub> = -50mA, I <sub>B</sub> = -1mA		_	-0.25	V
	RN2221		_	V <sub>CE</sub> = -0.2V I <sub>C</sub> = -100mA	-1.0	_	-3.5	V
Input voltage (ON)	RN2222	V <sub>I (ON)</sub>	_		-1.4	_	-4.5	
	RN2223		_		-2.0	_	-6.5	
	RN2224		_		-3.0	_	-12.0	
	RN2225		_		-0.6	_	-2.0	
	RN2226		_		-0.7	_	-2.5	
	RN2227		_		-1.0	_	-3.0	
Input voltage (OFF)	RN2221~2224	V <sub>I (OFF)</sub>	_	V <sub>CE</sub> = -5V, I <sub>C</sub> = -0.1mA	-0.8	_	-1.3	V
	RN2225, 2226		_		-0.4	_	-0.8	
	RN2227		_		-0.5	_	-1.0	
Translation frequency	RN2221~2227	f <sub>T</sub>	_	$V_{CE} = -5V, I_{C} = -20mA$	_	200	_	MHz
Collector output capacitance	RN2221~2227	C <sub>ob</sub>	_	$V_{CB} = -10V, I_{E} = 0$ f = 1MHz	_	13	_	pF
Input resistor	RN2221	R1	_	_	0.7	1.0	1.3	kΩ
	RN2222		_		1.54	2.2	2.86	
	RN2223		_		3.29	4.7	6.11	
	RN2224		_		7	10	13	
	RN2225		_		0.329	0.47	0.61	
	RN2226		_		0.7	1.0	1.3	
	RN2227		_		1.54	2.2	2.86	
Resistor ratio	RN2221~2224	R1/R2 —	_	_	0.9	1.0	1.1	_
	RN2225		_		0.0423	0.047	0.0517	
	RN2226		_		0.09	0.1	0.11	
	RN2227		_		0.2	0.22	0.24	

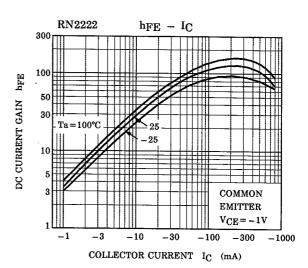


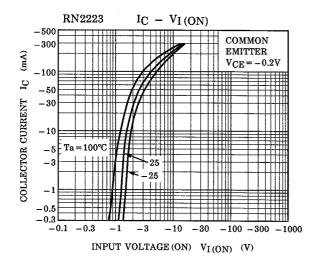


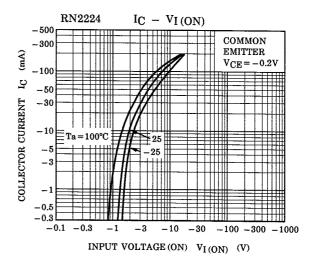


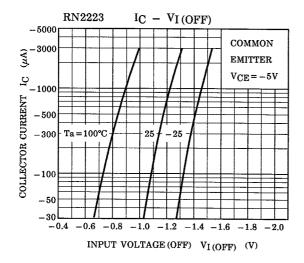


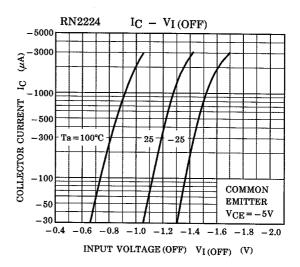


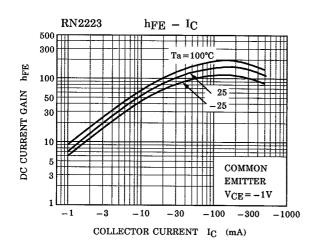


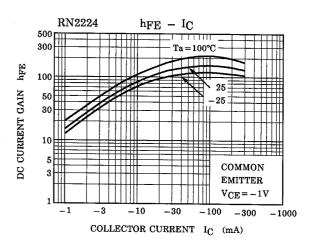


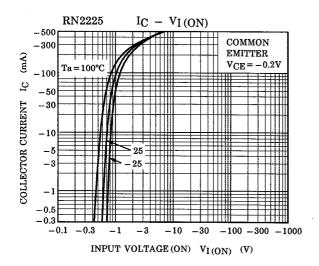


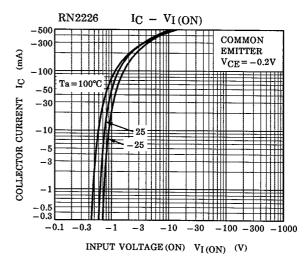


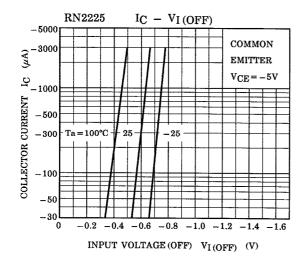


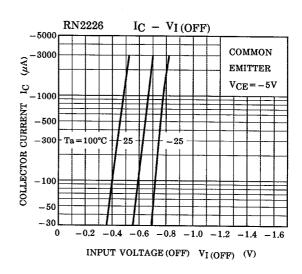


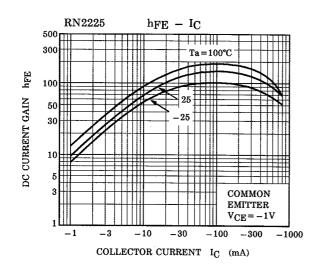


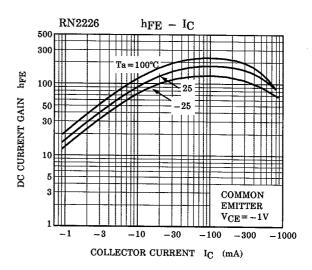


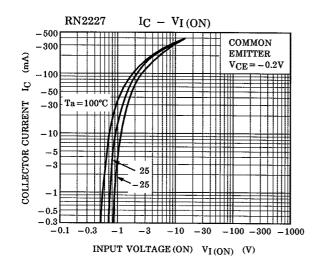


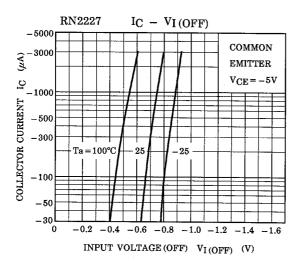


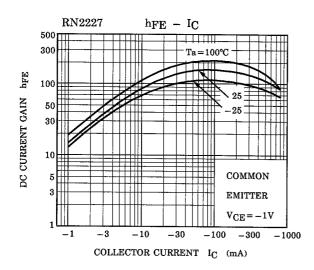












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